

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L2	3323	polysilicon with resistor	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/20 16:08
L3	1413	"polysilicon resistor"	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/20 16:06
L4	17169	implant\$4 same anneal\$3	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/20 13:04
L5	153	3 and 4	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/20 13:04
L6	1601	polysilicon same (implant\$4 or dop\$4) same (anneal\$3 or heat\$3) same (resistance or resistor)	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/20 16:05
L7	599	polysilicon same (implant\$4 or dop\$4) same (anneal\$3 or heat\$3) same (resistance or resistor) same gate	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/20 16:06
L8	269	polysilicon same (implant\$4 or dop\$4) same (anneal\$3 or heat\$3) same (resistance or resistor) same gate same silicid\$4	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/20 16:10
L12	307	polysilicon same (implant\$4 or dop\$4) same (anneal\$3 or heat\$3) same (resistance or resistor) same (SiN or nitride or SiON or "silicon nitride")	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/20 16:12